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(71) Applicant (for all designated States except US): **TOSOH SMD, INC.** [US/US]; 3600 Gantz Road, Grove City, OH 43123 (US).

(72) Inventors; and

(75) Inventors/Applicants (for US only): **WICKERSHAM,**

Charles, E., Jr. [US/US]; 571 Arden Road, Columbus, OH 43214 (US). **POOLE, John, E.** [US/US]; 6251 Mound View Place, Grove City, OH 43123 (US). **LEYBOVICH, Alexander** [US/US]; 5283 Gillette Avenue, Hilliard, OH 43026 (US). **ZHU, Lin** [US/US]; 3092 Wyandot Drive, Springfield, OH 45501 (US).

(74) Agents: **PEACOCK, Bruce, E.** et al.; Biebel & French, 35 East First Street, Dayton, OH 45402 (US).

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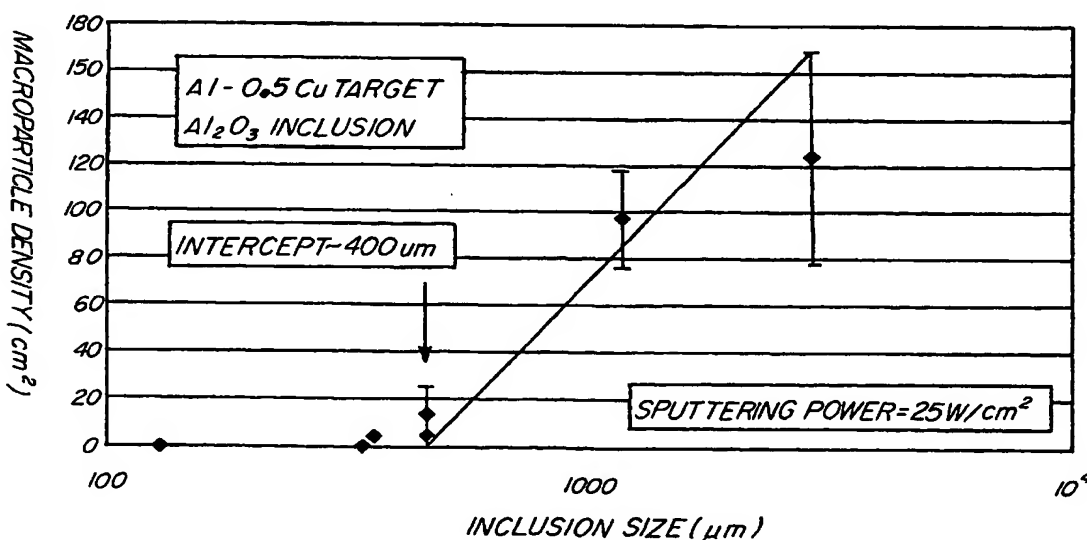
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(54) Title: SPUTTER TARGETS AND METHODS OF MANUFACTURING SAME TO REDUCE PARTICULATE EMISSION DURING SPUTTERING



(57) Abstract: Methods for reducing inclusion content of sputter targets and targets so produced are disclosed. Inclusions (93) may be reduced by adding a small amount of Si to the molten Al or molten Al alloy followed by filtering of the molten metals through a filter medium (175). Targets having substantially no inclusions (93) therein of greater than about 400μm are especially useful in the sputtering of large flat panel displays and result, upon sputtering, in a reduction in the amount of macroparticles sputtered onto the substrate.

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